



PMB072T045SS-255A

5A/45V⁽¹⁾, low VF Planar MOS barrier diode

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1828μm	72.0 mil
	Top Metal Pad Size (B)	1728μm	68.0mil
	Chip Size (C)	/	/
	Wafer Thickness (D)	255 μm	10.0 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	PMB072T045SS-255A	Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

Electrical Characteristics (T_J=25

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Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	46	52	-	V	I _R =300μA
V _F	Instantaneous Forward Voltage	-	0.42	0.46	V	I _F =5A ⁽³⁾
I _R	Reverse Leakage Current	-	30	120		V _R =45V
T _J , T _{STG}	Operating and Storage Temperature	-40°C to 150°C Max				

Note:

(1) The preliminary w3 29000008871 0 59.32 841.2 re6.0 222.77 Tm0 70008871 0 59.32 841.2 re1 05 (en-6) BDC 467.86 265.73 9.2 15() f02.3